

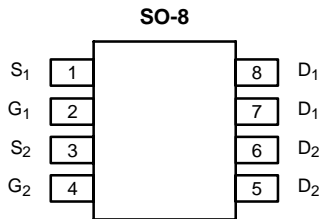


Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)
30	0.022 @ V _{GS} = 10 V	7.5
	0.030 @ V _{GS} = 4.5 V	6.5

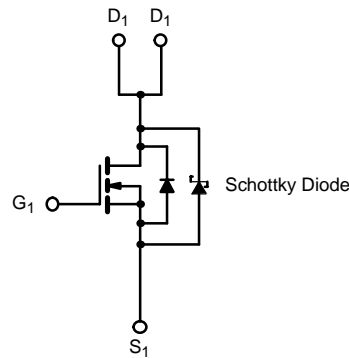
SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.50 V @ 1.0 A	2.0

LITTLE FOOT PLUS™

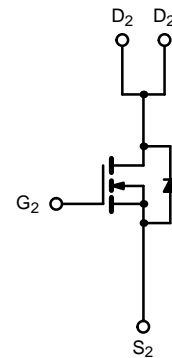


Top View

Ordering Information: Si4834DY
Si4834DY-T1 (with Tape and Reel)



N-Channel MOSFET



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	7.5	5.7	A
	T _A = 70 °C		6.0	4.6	
Pulsed Drain Current		I _{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	0.9	W
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2.0	1.1	
	T _A = 70 °C		1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	MOSFET		Schottky		Unit
			Typ	Max	Typ	Max	
Maximum Junction-to-Ambient ^a	t ≤ 10 sec	R _{thJA}	52	62.5	53	62.5	°C/W
	Steady-State		93	110	93	110	
Maximum Junction-to-Foot (Drain)		R _{thJC}	35	40	35	40	

Notes
a. Surface Mounted on 1" x 1" FR4 Board.

MOSFET SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED).						
Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.8			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V	Ch-1		100	μA
			Ch-2		1	
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 85 °C	Ch-1		2000	
			Ch-2		15	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	20			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 7.5 A		0.018	0.022	Ω
		V _{GS} = 4.5 V, I _D = 6.5 A		0.024	0.030	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 7.5 A		22		S
Diode Forward Voltage ^b	V _{SD}	I _S = 1 A, V _{GS} = 0 V	Ch-1	0.47	0.5	V
			Ch-2	0.8	1.2	
Dynamic^a						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 7.5 A		13	20	nC
Gate-Source Charge	Q _{gs}			2		
Gate-Drain Charge	Q _{gd}			2.7		
Gate Resistance	R _g		0.5	1.9	3.2	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω		8	16	ns
Rise Time	t _r			10	20	
Turn-Off Delay Time	t _{d(off)}			21	40	
Fall Time	t _f			10	20	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.7 A, di/dt = 100 A/μs	Ch-1	32	70	
			Ch-2	40	80	

Notes

- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

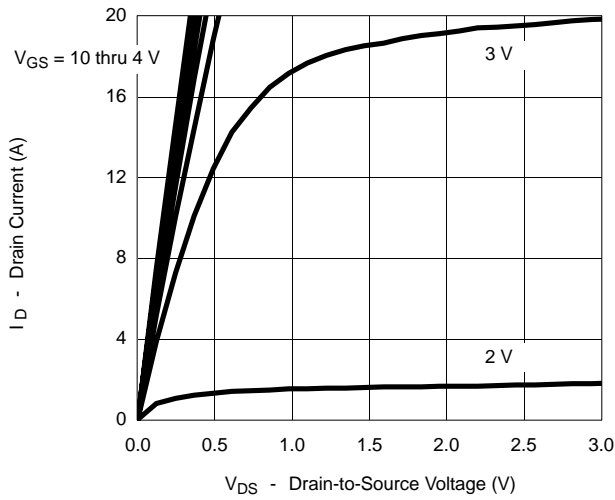
SCHOTTKY SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward Voltage Drop	V _F	I _F = 1.0 A		0.47	0.50	V
		I _F = 1.0 A, T _J = 125 °C		0.36	0.42	
Maximum Reverse Leakage Current	I _{rm}	V _r = 30 V		0.004	0.100	mA
		V _r = 30 V, T _J = 100 °C		0.7	10	
		V _r = -30 V, T _J = 125 °C		3.0	20	
Junction Capacitance	C _T	V _r = 10 V		50		pF



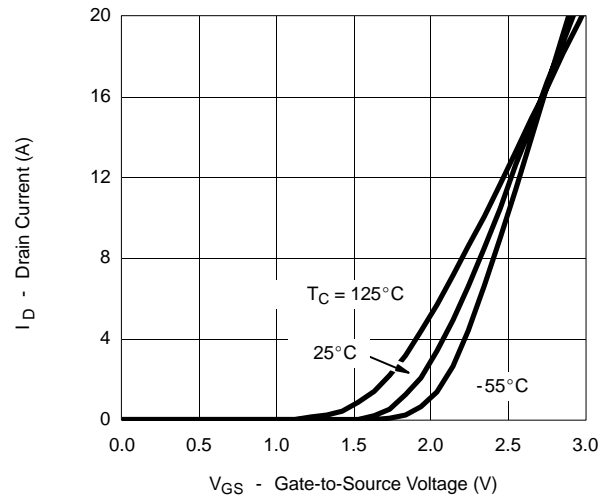
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

MOSFET

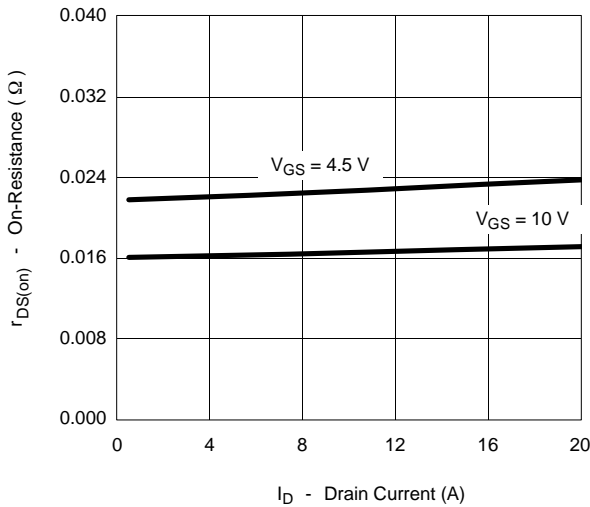
Output Characteristics



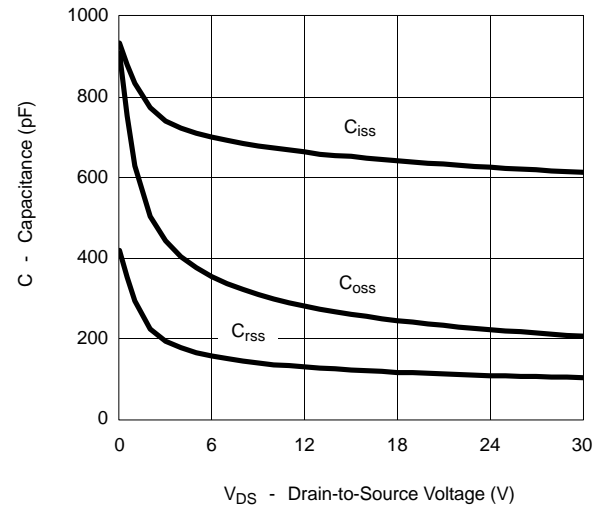
Transfer Characteristics



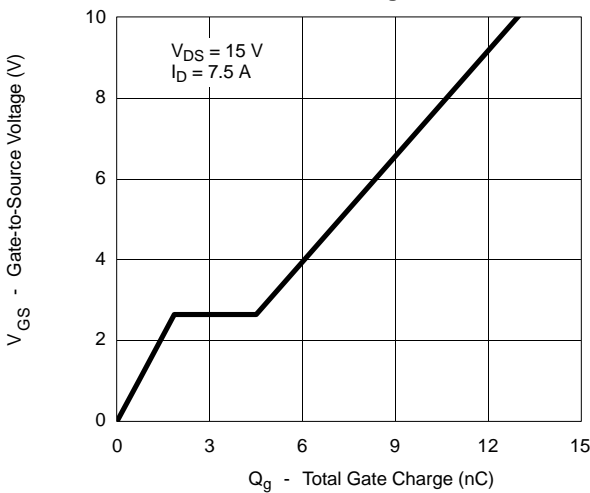
On-Resistance vs. Drain Current



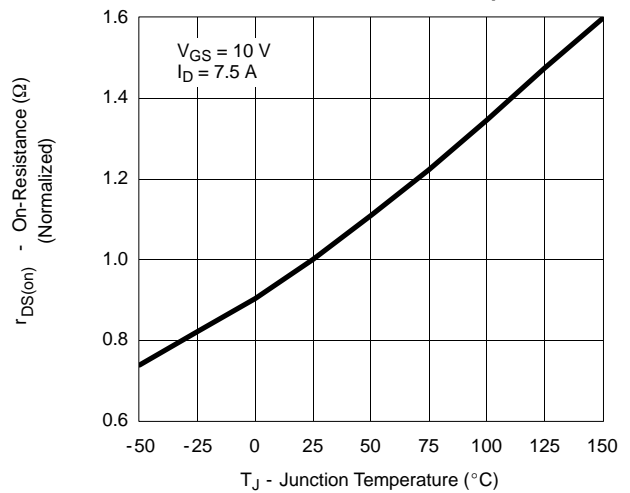
Capacitance



Gate Charge



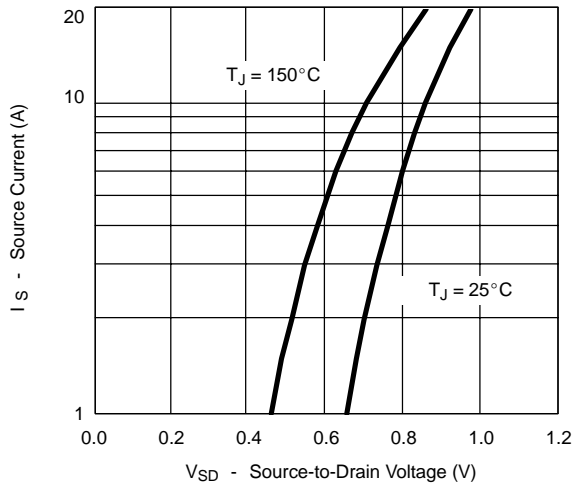
On-Resistance vs. Junction Temperature



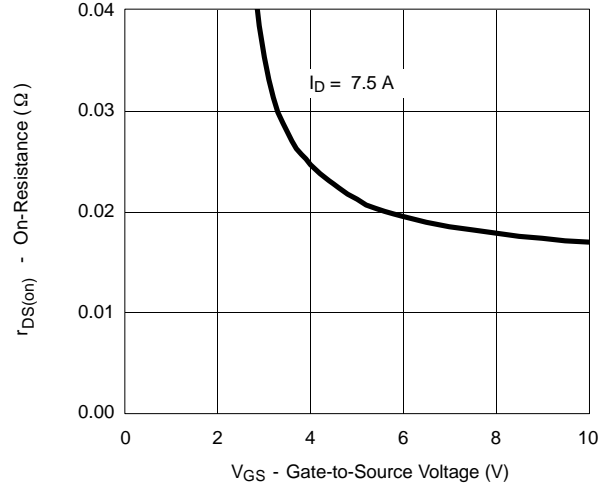
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

MOSFET

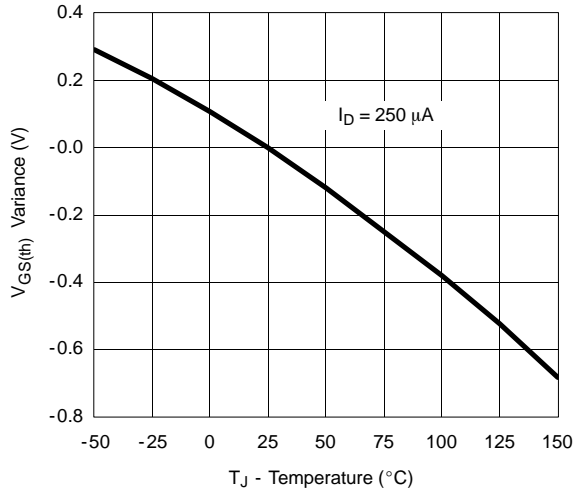
Source-Drain Diode Forward Voltage



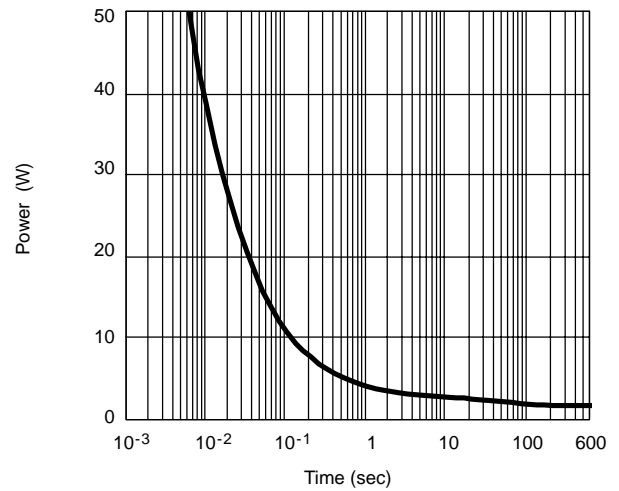
On-Resistance vs. Gate-to-Source Voltage



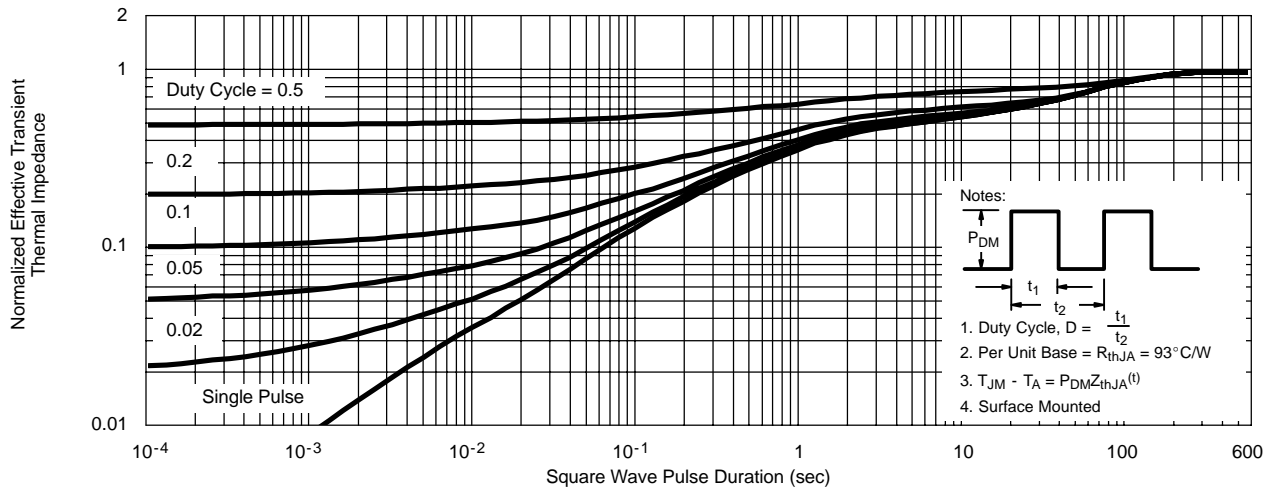
Threshold Voltage



Single Pulse Power

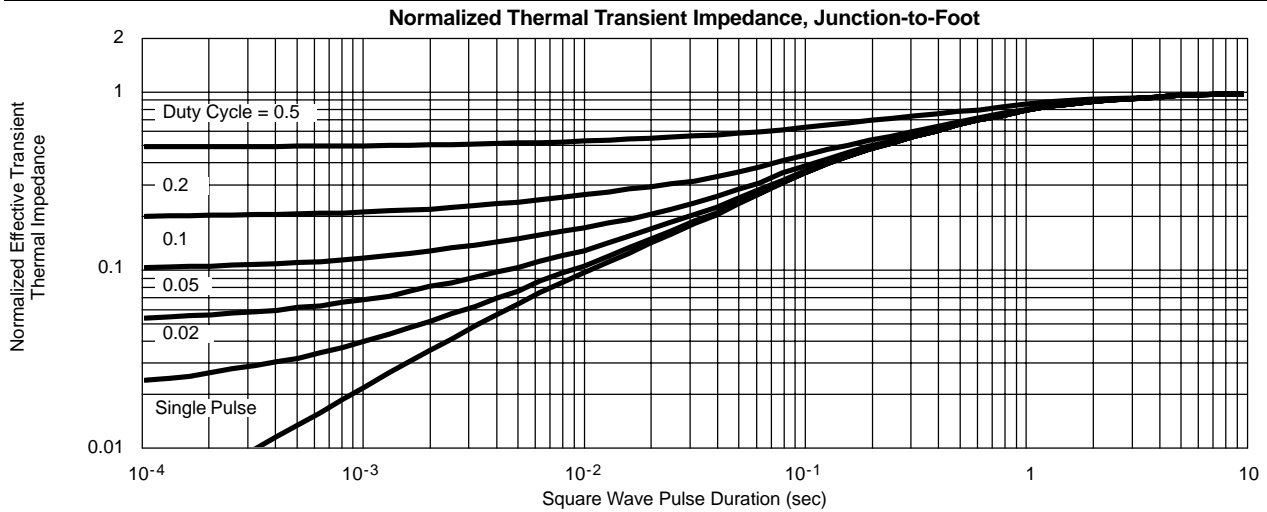


Normalized Thermal Transient Impedance, Junction-to-Ambient





TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) MOSFET



TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED) SCHOTTKY

